

AMENDMENTS TO THE CLAIMS:

The following listing of the claims replaces all prior versions, and listings, of the claims in the application:

1. (Currently Amended) A plasma treatment apparatus comprising:
a plasma generation unit comprising a first electrode and a plurality of second electrodes opposed to the first electrode;
a gas supply unit for ~~introducing~~ blowing a process gas into a space between the first electrode and the plurality of second electrodes ; and
a unit for selectively applying a voltage to at least one electrode among the plurality of second electrodes,
wherein the ~~plasma generation unit is~~ plurality of second electrodes are arranged linearly in one line or a plurality of lines.

2. (Currently Amended) A plasma treatment apparatus comprising:
a plasma generation unit comprising a first electrode and a plurality of second electrodes opposed to the first electrode;
a gas supply unit for ~~introducing~~ blowing a process gas into a space between the first electrode and the plurality of second electrodes; and
a unit for selectively applying a voltage to at least one electrode among the plurality of second electrodes,
wherein the plasma generation unit is arranged linearly in one line or a plurality of lines; and
wherein at least one of the plurality of second electrodes has a length of equal to or less than 1 mm on a side of an object to be treated.

3. (Currently Amended) A plasma treatment apparatus comprising:
a plasma generation unit comprising a first electrode and a plurality of second electrodes opposed to the first electrode for forming a pattern on an object to be treated;
a gas supply unit for ~~introducing~~ blowing a process gas into a space between the first electrode and the plurality of second electrodes; and

a unit for selectively applying a voltage to at least one electrode among the plurality of second electrodes,

wherein the plasma generation unit is arranged linearly in one line or a plurality of lines; and

wherein at least one of the plurality of second electrodes has a length of equal to or less than a square of a line width of the pattern on a side of the object to be treated.

4. (Original) A plasma treatment apparatus according to claim 3, wherein the pattern is a wiring pattern.

5. (Previously Presented) A plasma treatment apparatus according to claim 2 further comprising a unit for positioning plasma generation unit to the object to be treated.

6. (Previously Presented) A plasma treatment apparatus according to claim 3 further comprising a unit for positioning the plasma generation unit to the pattern on the object to be treated.

7. (Previously Presented) A plasma treatment apparatus according to claim 1, wherein the plasma generation unit comprises a plurality of plasma generators, each said plasma generator comprising said first electrode and one of the second electrodes, and relative scanning of the plasma generators is synchronized with the application of the voltage to a predetermined electrode among the plurality of second electrodes.

8. (Previously Presented) A plasma treatment apparatus according to claim 2, wherein the plasma generation unit comprises a plurality of plasma generators, each said plasma generator comprising said first electrode and one of the second electrodes, and relative scanning of the plasma generators is synchronized with the application of the voltage to a predetermined electrode among the plurality of second electrodes.

9. (Previously Presented) A plasma treatment apparatus according to claim 3, wherein the plasma generation unit comprises a plurality of plasma generators, each

said plasma generator comprising said first electrode and one of the second electrodes, and relative scanning of the plasma generators is synchronized with the application of the voltage to a predetermined electrode among the plurality of second electrodes.

10. (Previously Presented) A plasma treatment apparatus according to claim 1, wherein the plurality of second electrodes are processed by using a focused ion beam apparatus, photolithography, or a laser lithography apparatus.

11. (Previously Presented) A plasma treatment apparatus according to claim 2, wherein the plurality of second electrodes are processed by using a focused ion beam apparatus, photolithography, or a laser lithography apparatus.

12. (Previously Presented) A plasma treatment apparatus according to claim 3, wherein the plurality of second electrodes are processed by using a focused ion beam apparatus, photolithography, or a laser lithography apparatus.

13. (Previously Presented) A plasma treatment apparatus according to claim 1, wherein the first electrode and the plurality of second electrodes are covered with a dielectric.

14. (Previously Presented) A plasma treatment apparatus according to claim 2, wherein the first electrode and the plurality of second electrodes are covered with a dielectric.

15. (Previously Presented) A plasma treatment apparatus according to claim 3, wherein the first electrode and the plurality of second electrodes are covered with a dielectric.

16. (Previously Presented) A plasma treatment apparatus according to claim 1, wherein the voltage is applied to the at least one electrode for performing a film formation, an etching treatment, or a surface modification over an object to be treated.

17. (Previously Presented) A plasma treatment apparatus according to claim 2, wherein the voltage is applied to the at least one electrode for performing a film formation, an

etching treatment, or a surface modification over an object to be treated.

18. (Previously Presented) A plasma treatment apparatus according to claim 3, wherein the forming of the pattern is performed under atmospheric pressure or under pressure approximate to atmospheric pressure.

19. (Previously Presented) A plasma treatment apparatus according to claim 1 further comprising a stage to which an object to be treated is fixed, wherein a scanning of the stage is synchronized with the application of the voltage to the at least one electrode.

20. (Previously Presented) A plasma treatment apparatus according to claim 2 further comprising a stage to which the object is fixed, wherein a scanning of the stage is synchronized with the application of the voltage to the at least one electrode.

21. (Previously Presented) A plasma treatment apparatus according to claim 3 further comprising a stage to which the object is fixed, wherein a scanning of the stage is synchronized with the application of the voltage to the at least one electrode.

22. (Previously Presented) A plasma treatment apparatus according to claim 16, wherein the film formation, the etching treatment, or the surface modification is performed under atmospheric pressure or under pressure approximate to atmospheric pressure.

23. (Previously Presented) A plasma treatment apparatus according to claim 17, wherein the film formation, the etching treatment, or the surface modification is performed under atmospheric pressure or under pressure approximate to atmospheric pressure.

24. (Currently Amended) A plasma treatment apparatus comprising:
a plurality of plasma generation units each comprising a first electrode and a plurality

of second electrodes;

a gas supply unit for ~~introducing~~ blowing a process gas into a space between the first electrode and the plurality of second electrodes; and

a unit for selectively applying a voltage to at least one electrode among the plurality of second electrodes,

wherein the plurality of plasma generation units are arranged linearly in one line or a plurality of lines.

25. (Previously Presented) A plasma treatment apparatus according to claim 24, wherein a relatively scanning of the plurality of plasma generation units is synchronized with the application of the voltage to the predetermined electrode.

26. (Previously Presented) A plasma treatment apparatus according to claim 24, wherein the plurality of second electrodes are processed by using a focused ion beam apparatus, photolithography, or a laser lithography apparatus.

27. (Previously Presented) A plasma treatment apparatus according to claim 24, wherein the first electrode and the plurality of second electrodes are covered with a dielectric.

28. (Previously Presented) A plasma treatment apparatus according to claim 24, wherein the voltage is applied to the predetermined electrode for performing a film formation, an etching treatment, or a surface modification over an object to be treated.

29. (Previously Presented) A plasma treatment apparatus according to claim 24 further comprising a stage to which an object to be treated is fixed, wherein a scanning of the stage is synchronized with the application of the voltage to the predetermined electrode.

30. (Previously Presented) A plasma treatment apparatus according to claim 28, wherein the film formation, the etching treatment, or the surface modification is performed under atmospheric pressure or under pressure approximate to atmospheric pressure.

31. (New) A plasma treatment apparatus comprising:
a plasma generation unit comprising a first electrode and a plurality of second electrodes opposed to the first electrode;
a gas supply unit for blowing a process gas to a substrate to be treated through a space between the first electrode and the plurality of second electrodes; and
a unit for selectively applying a voltage to at least one electrode among the plurality of second electrodes,
wherein the plurality of second electrodes are arranged linearly in one line or a plurality of lines.

32. (New) A plasma treatment apparatus according to claim 31,
wherein a relatively scanning of the plurality of plasma generation units is synchronized with the application of the voltage to the predetermined electrode.

33. (New) A plasma treatment apparatus according to claim 31, wherein the plurality of second electrodes are processed by using a focused ion beam apparatus, photolithography, or a laser lithography apparatus.

34. (New) A plasma treatment apparatus according to claim 31, wherein the first electrode and the plurality of second electrodes are covered with a dielectric.

35. (New) A plasma treatment apparatus according to claim 31, wherein the voltage is applied to the predetermined electrode for performing a film formation, an etching treatment, or a surface modification over an object to be treated.

36. (New) A plasma treatment apparatus according to claim 31 further comprising a stage to which an object to be treated is fixed,
wherein a scanning of the stage is synchronized with the application of the voltage to the predetermined electrode.

37. (New) A plasma treatment apparatus according to claim 35, wherein the film formation, the etching treatment, or the surface modification is performed under atmospheric pressure or under pressure approximate to atmospheric pressure.